Abstracts

Physical scaling rules for AlGaAs/GaAs power HBTs based on a small-signal equivalent circuit

U. Schaper and P. Zwicknagl. "Physical scaling rules for AlGaAs/GaAs power HBTs based on a small-signal equivalent circuit." 1998 Transactions on Microwave Theory and Techniques 46.7 (Jul. 1998 [T-MTT]): 1006-1009.

Physical scaling rules for AlGaAs/GaAs heterojunction bipolar transistors (HBTs) containing 2-16 emitter fingers are demonstrated, the parameter extraction is based on a small signal equivalent circuit. The scaling parameters compare favorably with the measured data from the process control monitor.

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